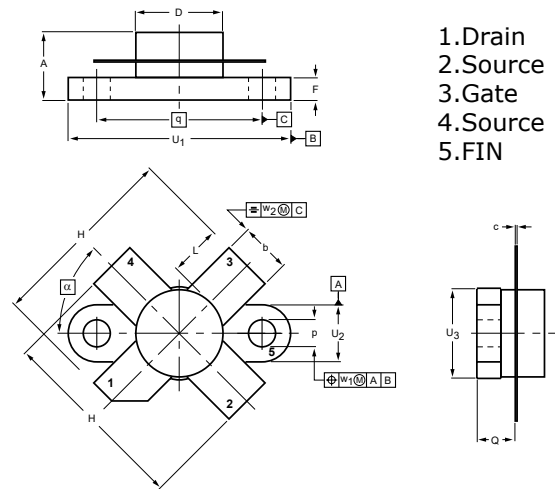


DESCRIPTION

Silicon N-channel enhancement mode vertical D-MOS transistor designed for large signal amplifier applications in the scope of 30-500Mhz

FEATURES

- Output Power: 20 W
- Power Gain: 17 dB Typ@400M, 28V
- Efficiency: 55% Typ



DIMENSIONS

NOTE: ALL ELECTRODES ARE ISOLATED FROM FLANGE.

UNIT	A	b	c	D	D ₁	F	H	L	p	Q	q	U ₁	U ₂	U ₃	w ₁	w ₂	α
mm	7.47 6.37	5.82 5.56	0.18 0.10	9.73 9.47	9.63 9.42	2.72 2.31	20.71 19.93	5.61 5.16	3.33 3.04	4.63 4.11	18.42	25.15 24.38	6.61 6.09	9.78 9.39	0.51	1.02	45°
inches	0.294 0.251	0.229 0.219	0.007 0.004	0.383 0.373	0.397 0.371	0.107 0.091	0.815 0.785	0.221 0.203	0.131 0.120	0.182 0.162	0.725	0.99 0.96	0.26 0.24	0.385 0.370	0.02	0.04	

MAXIMUM RATINGS

CHARACTERISTICS	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	V _{DSS}	65	V
Gate-Source Voltage	V _{GS}	±40	V
Drain Current — Continuous	I _D	4	A
Total Device Dissipation	P _D	70	W
Junction Temperature	T _J	200	°C
Storage Temperature Range	T _{STG}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX	UNITS
Drain-Source Breakdown Voltage	V _{(BR)DSS}	I _D =5mA, V _{GS} =0	65	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} =0V, V _{DS} =28V	-	-	1	mAdc
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±40V, V _{DS} =0V	-	-	1	uAdc
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = 10 V, I _D = 25mA	1.0	-	6.0	V
Forward Transconductance	g _{fs}	V _{DS} = 10 V, I _D = 1.5A	600	800	-	mhos
Input Capacitance	C _{iss}	V _{DS} = 28 V, V _{GS} = 0 V, f = 1.0 MHz	-	45	-	pF
Output Capacitance	C _{oss}		-	38	-	pF
Reverse Transfer Capacitance	C _{rss}		-	3.8	-	pF
Common Source Power Gain	G _P	V _{DD} =28V, P _{OUT} =20W,	14.0	17.0	-	dB
Drain Efficiency	η _D	f=400MHz	50	55.0	-	%

Note : Above parameters , ratings , limits and conditions are subject to change.